

## PNP MJ3000 - MJ3001

# **COMPLEMENTARY POWER DARLINGTONS**

The MJ3000, and MJ3001 are silicon epitaxial-base PNP power transistors in monolithic Darlington configuration and are mounted in Jedec TO-3 metal case. They are intented for use in power linear and switching applications.

The complementary PNP types are the MJ2500 and MJ2501 respectively Compliance to RoHS

### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Ratings			Value	Unit	
V <sub>CBO</sub>	Collector-Base Voltage	I <sub>E</sub> =0	MJ3000	60	V	
		IE=0	MJ3001	80	V	
V <sub>CEO</sub>	Collector-EmitterVoltage		MJ3000	60	V	
		I <sub>B</sub> =0	MJ3001	80	V	
V <sub>EBO</sub>	Emitter-Base Voltage	1 -0	MJ3000	5.0	V	
		I <sub>C</sub> =0	MJ3001			
	Collector Current	MJ30	MJ3000	10	А	
Ic	Collector Current		MJ3001	10	^	
I <sub>B</sub>	Base Current		MJ3000	0.2	Α	
	base Current		MJ3001	0.2	A	
D	Power Dissipation	@ T . 25°	MJ3000	150	W	
P <sub>T</sub>		@ T <sub>C</sub> < 25°	MJ3001			
TJ	'		MJ3000	200	°C	
Ts			MJ3001	-65 to +200		

### THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R <sub>thJ-C</sub>	Thermal Resistance, Junction to Case 1.17 °		°C/W



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### **ELECTRICAL CHARACTERISTICS**

TC=25°C unless otherwise noted

Symbol	Ratings	Test Cond	lition(s)	Min	Тур	Max	Unit
BV <sub>CEO</sub>	Collector-Emitter Breakdown	I <sub>C</sub> =100mA	MJ3000	60	-	-	V
PACEO	Voltage (*)	$I_B=0$	MJ3001	80	-	-	V
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> =30 V I <sub>B</sub> =0	MJ3000	ı	-	1.0	mA
		V <sub>CE</sub> =40 V I <sub>B</sub> =0	MJ3001	1			
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>BE</sub> =5.0 V	MJ3000	_	-	2.0	mA
		$I_{C}=0$	MJ3001				
I <sub>CER</sub>	Collector-Emitter Leakage Current	$V_{CB}$ =60 V $R_{BE}$ =1.0 kΩ	MJ3000	1	-	4.0	
		$V_{CB}$ =80 V $R_{BE}$ =1.0 kΩ	MJ3001	-	-	1.0	
		$V_{CB}$ =60 V $R_{BE}$ =1.0 k $\Omega$ $T_{C}$ =150°C	MJ3000	-	-	F.0	mA
		$V_{CB}$ =80 V $R_{BE}$ =1.0 k $\Omega$ $T_{C}$ =150°C	MJ3001	-	-	5.0	
V <sub>CE(SAT)</sub>	Collector-Emitter saturation Voltage (*)	I <sub>C</sub> =5.0 A I <sub>B</sub> =20 mA	MJ3000 MJ3001	-	-	2.0	V
		I <sub>C</sub> =10 A I <sub>B</sub> =50 mA	MJ3000 MJ3001	-	-	4.0	
V <sub>BE</sub>	Base-Emitter Voltage (*)	I <sub>C</sub> =5.0 A V <sub>CE</sub> =3.0V	MJ3000 MJ3001	-	-	3	V
h <sub>FE</sub>	DC Current Gain (*)	V <sub>CE</sub> =3.0 V I <sub>C</sub> =5.0 A	MJ3000 MJ3001	1000	-	-	-

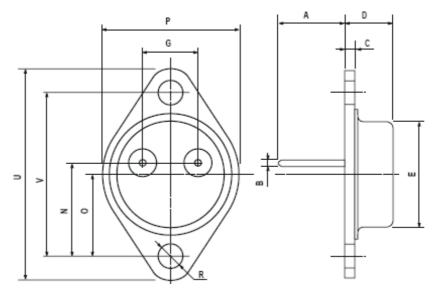
<sup>(\*)</sup> Pulse Width  $\approx$  300  $\mu$ s, Duty Cycle  $\angle$  2.0%



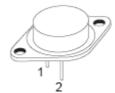
### PNP MJ3000 - MJ3001

### MECHANICAL DATA CASE TO-3

DIMENSIONS (mm)				
	min	max		
A	11	13.10		
В	0.97	1.15		
С	1.5	1.65		
D	8.32	8.92		
F	19	20		
G	10.70	11.1		
N	16.50	17.20		
Р	25	26		
R	4	4.09		
U	38.50	39.30		
V	30	30.30		



Pin 1 :	Base
Pin 2 :	Emitter
Case:	Collector



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